#### Low-Power High-Precision Crystal Oscillators

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# CSPT

# LOW-POWER HIGH-PRECISION CRYSTAL OSCILLATORS

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- Crystal resonator.
- General theory of crystal oscillators
  - splitting for analysis
  - oscillation: condition and frequency
  - amplitude limitation
  - start-up time.
- Theory of the 3-point oscillator
  - linear analysis with and without losses
  - nonlinear behaviour
  - amplitude and energy of oscillation
  - frequency stability, frequency tuning
  - phase noise
  - elimination of unwanted modes
  - loading by amplifier.
- Practical implementations
  - grounded drain oscillator
  - grounded source oscillators
  - amplitude regulator
  - circuit examples.

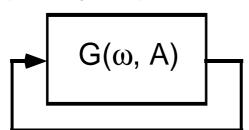
#### APPLICATIONS OF CRYSTAL OSCILLATORS

- Time-keeping (real-time clocks, RTC)
  - precision and stability: 10<sup>-6</sup>
     ( ≅ 30s/year)
  - low power watches: ≤ 0.5 μW
- Radio communication
  - precision and stability: 10<sup>-6</sup> to 10<sup>-5</sup>
     (1 to 10kHz at 1GHz)
  - low power («1mW)
  - phase noise if :
    - no VCO (direct RF generation)
    - injection synchronized VCO
    - wide-band PLL loop
       otherwise negligible (~1/Q²)
- Clock of analog systems (filters)
  - precision and stability: 10<sup>-4</sup> (better than component mismatch)
- Clock of digital systems
  - no high precision required
  - beware of overtone oscillation!

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#### BASICS ON OSCILLATORS

Frequency-dependent nonlinear loop.



$$\omega$$
 = (angular) frequency

A = amplitude

- strongly nonlinear: relaxation oscillator
- weakly nonlinear: harmonic oscillator
- Stable oscillation at frequency  $\omega_0$ :  $G(\omega_0, A_0) = 1$

with:

$$\frac{d(Arg(G))}{d\omega}\Big|_{\substack{\omega=\omega_0\\A=A_0}} < 0$$

(phase stability)

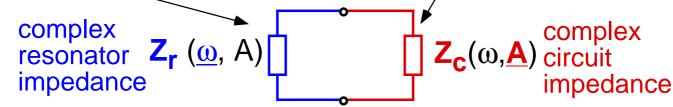
and:

$$\frac{\mathsf{d}|\mathsf{G}|}{\mathsf{d}\mathsf{A}}\bigg|_{\substack{\omega=\omega_0\\\mathsf{A}=\mathsf{A}_0}}<0$$

(amplitude stability)

Alternative representation:

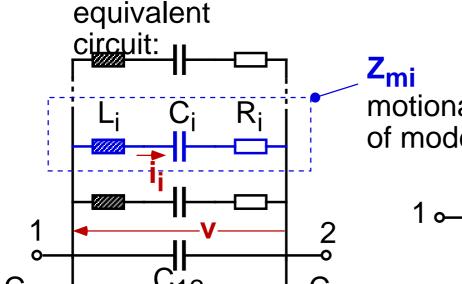
Resonator and sustaining circuit



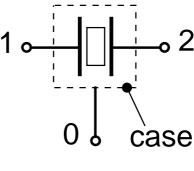
Stable oscillation at frequency ω<sub>0</sub>:

$$\mathbf{Z_r}(\omega_0, A_0) + \mathbf{Z_c}(\omega_0, A_0) = 0$$

#### CRYSTAL RESONATOR



<sup>4</sup>mi motional impedance of mode *i* 



- Mechanical resonant frequency :  $\omega_{mi} = \frac{1}{\sqrt{L_i C_i}}$
- Mechanical quality factor:

$$Q_i = \frac{1}{\omega_{mi}C_iR_i} *1$$

- i<sub>i</sub> ~ velocity ~amplitude of mode i
- C<sub>i</sub> ~ electromech. coupling of mode i, C<sub>i</sub>«C<sub>12</sub>
- ω<sub>mi</sub> of different modes are not exact multiples of each other, and Q<sub>i</sub>»1; therefore:

even if v(t) is strongly distorted

all branches other than Z<sub>mi</sub> are negligible

(for a single mode i of oscillation), and

the motional current ii is always sinusoidal

#### MECHANICAL POWER AND ENERGY

Mechanical energy of oscillation:

$$E_{m} = \frac{\stackrel{\wedge}{I^{2}}}{2} = \frac{\stackrel{\wedge}{I^{2}}}{2\omega_{m}^{2}C}$$

must be limited to avoid destruction, aging, and nonlinear effects.

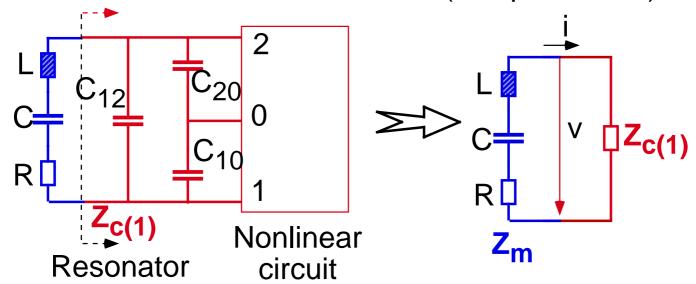
Mechanical power dissipation:

$$P_{m} = \frac{R\hat{I}^{2}}{2} = \frac{\hat{I}^{2}}{2\omega_{m}QC}$$

 Can be calculated as soon as the peak value Î of sinusoidal current i(t) is known.

## GENERAL FORM OF CRYSTAL OSCILLATOR

 The resonator is combined with an active circuit to sustain oscillation (compensate R)



- Frequency of oscillation  $\omega$  slightly different of  $\omega_m$  (effect of circuit)
- Frequency pulling  $\mathbf{p} = \frac{\omega \omega_{m}}{\omega_{m}}$  « 1
- The system must be conceptually split into:

Motional impedance 
$$Z_m = R + j \frac{2p}{\omega C}$$
 (linear, strongly dependent on p)

Circuit impedance Z<sub>c(1)</sub>, independent of p

Since no energy can be exchanged at harmonic frequencies (i sinusoidal), nonlinear effects are included by defining the circuit impedance at fundamental frequency:

$$Z_{c(1)} = \frac{V_{(1)}}{I}$$

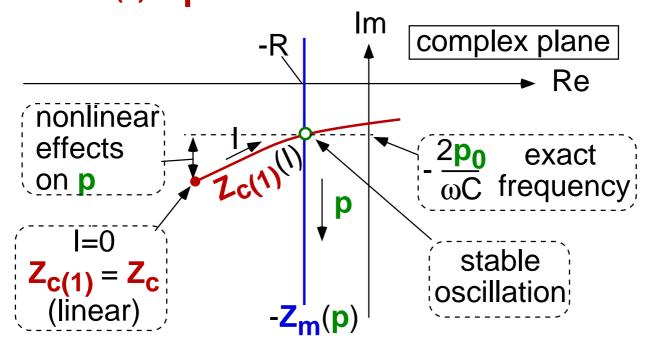
where  $V_{(1)}$  is the complex value of the fundamental of v for complex value I of sinusoidal current i.

#### **OSCILLATION**

Stable oscillation:

$$Z_{m} + Z_{c(1)} = 0$$
 $Re|Z_{c(1)}| = -R$ 
 $Im|Z_{c(1)}| = -\frac{2p_{0}}{\omega C}$ 

where  $Z_{c(1)} = \frac{V_{(1)}}{I}$  circuit imped. at fundam. frequency



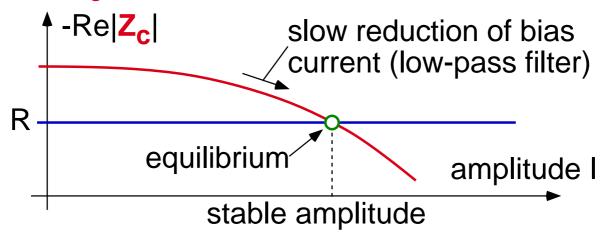
- Growth of oscillation: exponential, with time constant  $\tau = \frac{2L}{Re|Z_{c(1)}|}$  - R
- Critical condition for start-up of oscillation:

$$Z_m + Z_c = 0$$

(linear circuit)

#### AMPLITUDE LIMITATION

- Necessary to define amplitude (an oscillator is always non linear)
- Instantaneous limitation by distortion:
  - → creates harmonics
    - → inter-modulation
      - → addit. fundam. component of current
        - → frequency change
          - → poor stability
    - → power dissipated in harmonics.
- Non-distorting amplitude limitation:
  - Z<sub>c</sub> linear but slowly variable.

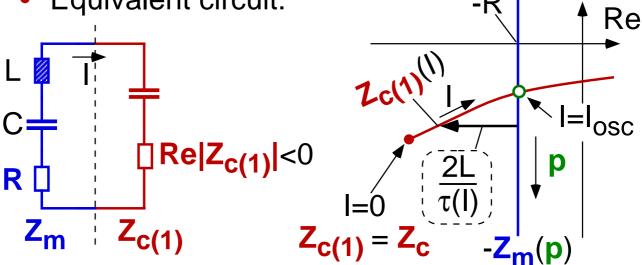


- + improved stability
- + reduced power dissipation in circuit (just above critical condition).

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#### START-UP TIME OF OSCILLATOR

• Equivalent circuit:

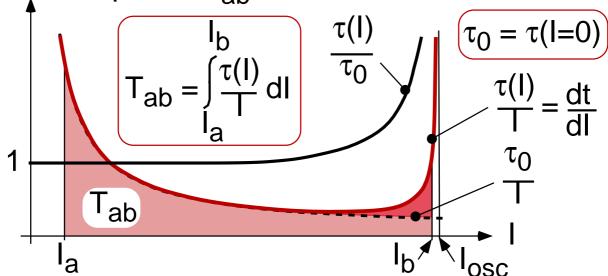


Growth of oscillation:

$$I = I_0 e^{t/\tau(I)} \quad \text{with } \tau(I) = \frac{2L}{-Re|Z_{c(1)}| - R}$$

$$\frac{dI}{dt} = \frac{I}{\tau(I)} \quad \longrightarrow \quad \left(\frac{dt}{dI} = \frac{\tau(I)}{I}\right)$$

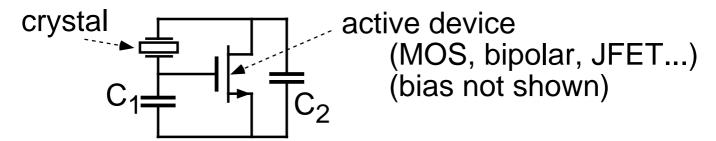
Start-up time T<sub>ab</sub> from I<sub>a</sub>(noise) to I<sub>b</sub>



• Approximation:  $T_{ab} = \tau_0 \ln(I_b/I_a)$ 

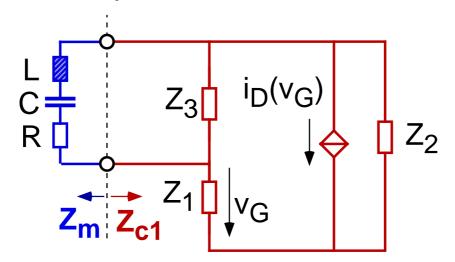
#### BASIC 3-POINT OSCILLATOR

 Only possibility to use a single active device when no inductance is available:



C<sub>1</sub>,C<sub>2</sub> are necessary functional capacitors.

• General equivalent circuit:

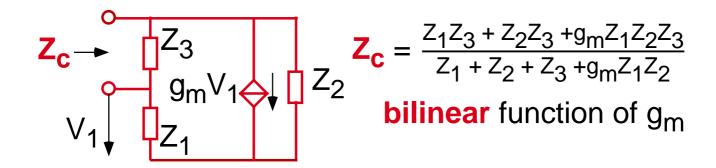


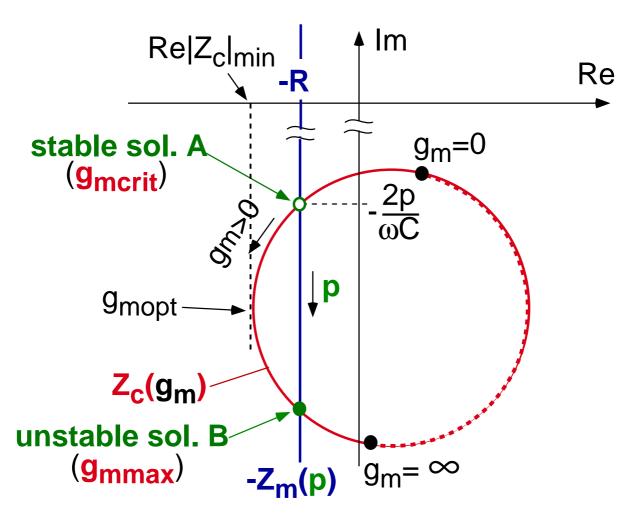
where  $Z_i^{-1} = G_i + j\omega C_i$  (independent of **p**)

- include all circuit losses
- may be nonlinear.

#### LINEAR ANALYSIS

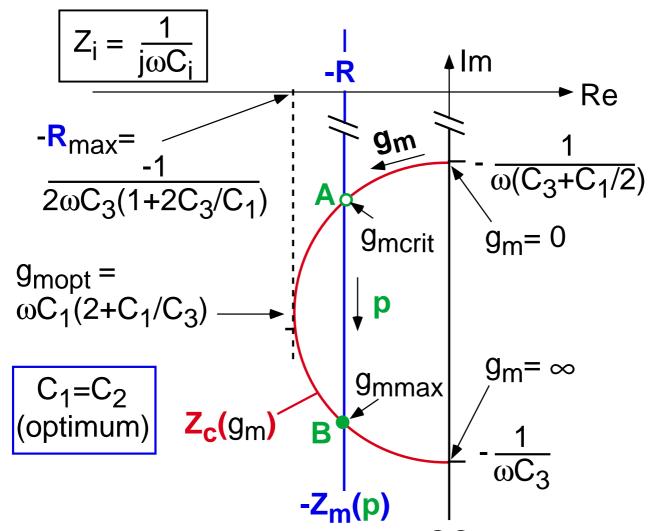
- $Z_{c1} \rightarrow Z_c$  and  $i_D(v_1) \rightarrow g_m V_1$
- General form of circuit (all losses included):





No oscillation if g<sub>m</sub> too small or too large.

#### LOSSLESS LINEAR ANALYSIS



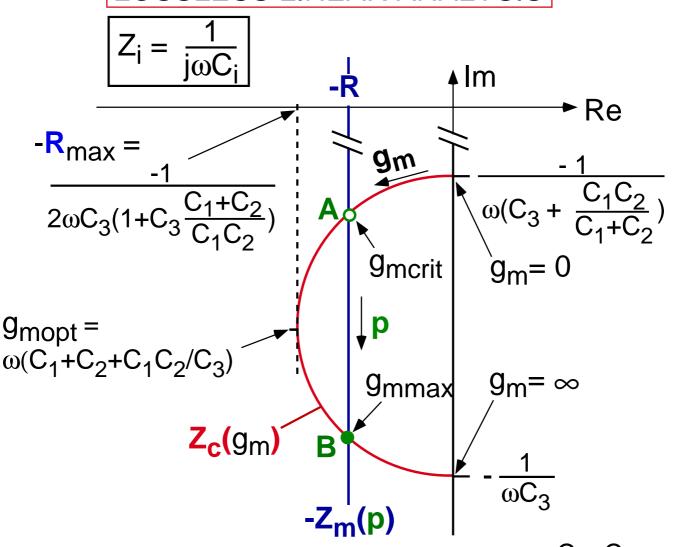
- Oscillation **only possible** if:  $\frac{QC}{C_3} > 2(1+2C_3/C_1)$ If large margin to minimize dp/dR, then:
  - $p_0 = \frac{\omega_0 \omega_m}{\omega_m} \cong \frac{C}{2C_3 + C_1}$  

    \* trade-off
  - $g_{mcrit} \cong \frac{\omega}{QC} (C_1 + 2C_3)^2 = \frac{\omega C}{Qp_0^2}$
  - $g_{mmax} \cong \omega C \ C_1^2 Q/C_3^2$  for  $C_3 \ll C_4$  thus:  $\frac{g_{mmax}}{g_{mcrit}} \cong \left[\frac{C \ C_1 \ Q}{C_3(C_1 + 2C_3)}\right]^2 \cong \left[\frac{QC}{C_3}\right]^2$

E. Vittoz, 2001.

#### LOSSLESS LINEAR ANALYSIS

OSC-8a



• Oscillation **only possible** if:  $\frac{QC}{C_3} > 2(1+C_3\frac{C_1+C_2}{C_1C_2})$ If large margin to minimize dp/dR, then:

• 
$$p_0 = \frac{\omega_0 - \omega_m}{\omega_m} \cong \frac{C}{2(C_3 + \frac{C_1 C_2}{C_1 + C_2})}$$
 trade-off  $C_1 = C_2$ 

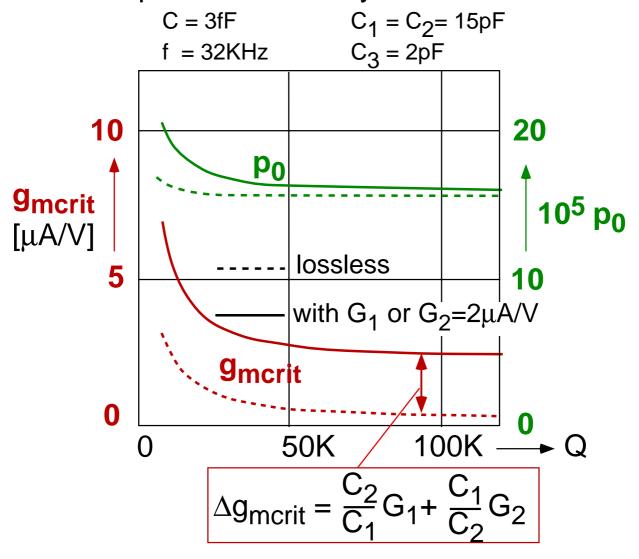
• 
$$g_{mcrit} \cong \frac{\omega}{QC} = \frac{(C_1C_2 + C_2C_3 + C_3C_1)^2}{C_1C_2} = \frac{\omega C}{Qp_0^2} = \frac{(C_1 + C_2)^2}{4C_1C_2}$$

• 
$$g_{\text{mmax}} \cong \omega C C_1 C_2 Q/C_3^2$$
 for  $C_3 \ll C_1$  and  $C_2$ 

thus: 
$$\frac{g_{mmax}}{g_{mcrit}} \cong \left[\frac{C C_1 C_2 Q}{C_3 (C_1 C_2 + C_2 C_3 + C_3 C_1)}\right]^2 \stackrel{\checkmark}{=} \left[\frac{QC}{C_3}\right]^2$$
E. Vittoz, 2001

#### EFFECT OF LOSSES

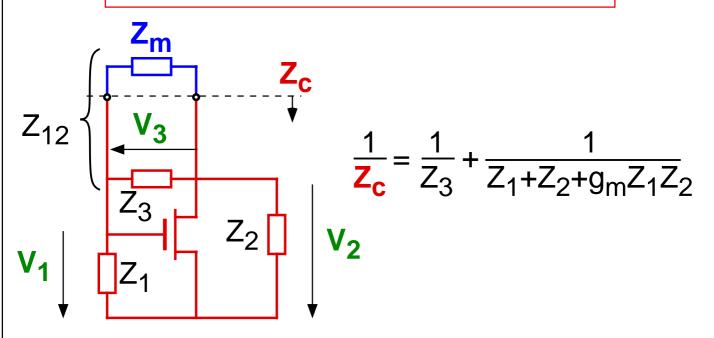
Example of linear analysis with:



- Causes of losses:
  - biasing circuitry
  - loading by amplifier
  - series resistance of capacitors (HF)
  - output conductance of active device
  - input conductance of active device (bipolar)
  - external load (moisture)

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# RELATIVE VOLTAGE AMPLITUDES



• Critical oscillation: 
$$Z_m = -Z_c$$
  
thus:  $1/7_{+0} = 1/7_{-} + 1/7_{0} = -1/7_{-} + 1/7_{0}$ 

thus:  $1/Z_{12} = 1/Z_m + 1/Z_3 = -1/Z_c + 1/Z_3$ 

yields:  $Z_{12} = -(Z_1 + Z_2 + g_{mcrit}Z_1Z_2)$ 

$$1+Z_{12}/Z_1 = V_2/V_1 = -Z_2(1/Z_1 + g_{mcrit})$$

$$V_3/V_1 = V_2/V_1 - 1$$

• Losselss circuit  $(Z_i = 1/j\omega C_i)$  with R«R<sub>max</sub>

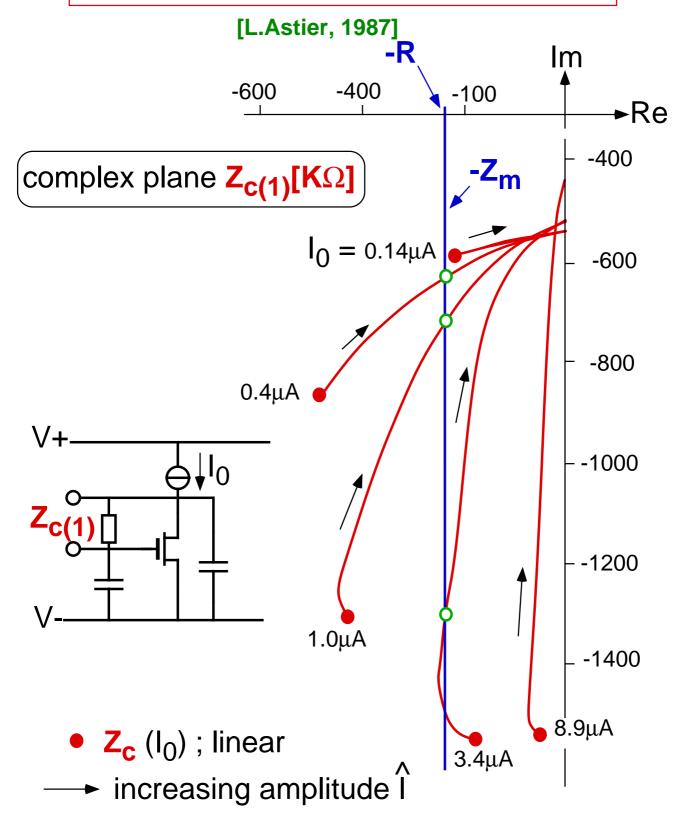
$$g_{mcrit} = \frac{\omega}{QC} \frac{(C_1C_2 + C_2C_3 + C_3C_1)^2}{C_1C_2}$$

yields: 
$$\frac{V_2}{V_1} = -\frac{C_1}{C_2} + j\frac{C_1}{QC}(1 + \frac{C_3}{C_1} + \frac{C_3}{C_2})^2$$

usually < or « 1

Then:  $V_2/V_1 \cong -C_1/C_2$  and  $V_3/V_1 \cong -(1+C_1/C_2)$ 

#### **EXAMPLE OF NONLINEAR ANALYSIS**

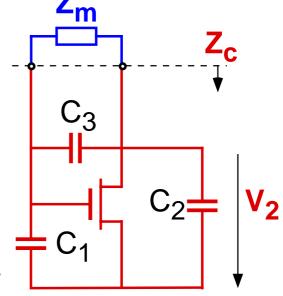


stable oscillation for particular value of R

#### DISTORTION OF GATE SIGNAL

Drain current is distorted

V<sub>2</sub> is distorted



- Drain to gate attenuation:
  - for fundamental frequency: F = (as shown before)
  - for harmonic components: H =  $(Z_m = \infty)$
  - relative attenuation  $\left| \frac{H}{F} \right| = \frac{C_3 C_1}{(C_1 + C_3)C_2}$ usually « 1, thus V<sub>1</sub> approximately sinusoidal
- Effect of residual distortion of  $V_1$ :
  - intermodulation of harmonics in transistor creation of out -of-phase fund. in drain
    - current
- change in p,  $\Rightarrow$  frequency instability  $C_3$  must therefore be minimized ( $Z_3$  large)

# AMPLITUDE LIMITATION BY i<sub>D</sub>(v<sub>G</sub>)

- Small effect on **p** (none if  $Z_3 = \infty$ ).
- Assumption: AC signal at gate sinusoidal:
   v<sub>G</sub> =V<sub>0</sub>+V<sub>1</sub>sinωt

Results in:  $i_D = f(v_G) = I_0 + I_1 \sin \omega t + harmonics$ 

then:  $I_1/V_1 = g_{m1}(V_1) = g_{mcrit}$ 

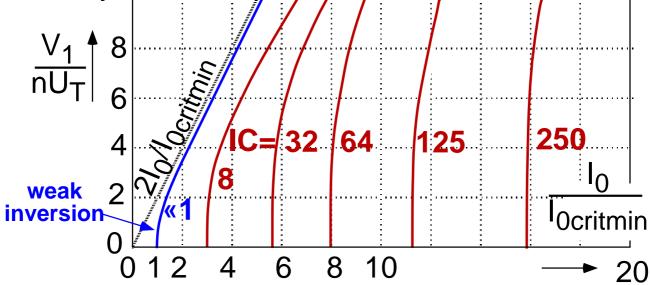
transconductance for fundamental frequency

for stable oscillation

Using continuous model for saturated MOS

$$i_D = I_S \ln^2(1 + e^{V/2})$$
 [Vittoz, 1994] [Enz et al., 1995]

where  $v = (v_{GS}-V_T)/(nU_T)$  and  $I_S = 2n\beta U_T^2$  this yields [L.Astier, 1987, von Kaenel et al.1995]:



 $V_1$  = peak voltage amplitude at gate of transistor

 $I_0$  = bias current of transistor

 $I_{\text{Ocritmin}} = nU_{\text{T}}g_{\text{mcrit}}$ 

 $IC = I_{0crit}/I_{S} = inversion coefficient at I_{0crit}$ 

I<sub>0</sub> (V<sub>1</sub>) is minimum in weak inversion (I<sub>0critmin</sub>).

#### AMPLITUDE OF OSCILLATION

- Limitation by nonlinear i<sub>D</sub>(v<sub>G</sub>) only
  - → Very small effect on frequency pulling **p** (none if  $Z_3 = \infty$ ).
- Goal: minimum current to produce g<sub>mcrit</sub>:
  - → transistor operated in weak inversion:

$$i_D = A \exp(v_G/nU_T)$$
 (with n=1.4...1.6)

Assumption: AC signal at gate sinusoidal:

$$v_G = V_0 + V_1 \sin(\omega t)$$

results in:  $i_D = I_0 + I_1 \sin(\omega t) + \text{harmonics}$ 

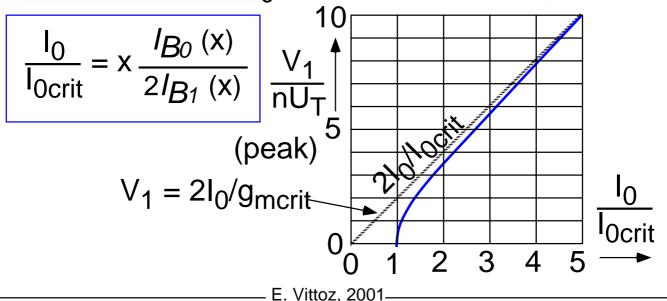
where: 
$$I_1 = I_0 \frac{2I_{B_1}(x)}{I_{B_0}(x)}$$
 with  $x = V_1/nU_T$ 

and  $I_{Bk}(x)$  are modified Bessel functions of order k

Transonductance g<sub>m1</sub> for the fundamental:

$$g_{m1} = I_1/V_1 = g_{mcrit} = I_{0crit}/(nU_T)$$
  
stable oscillation

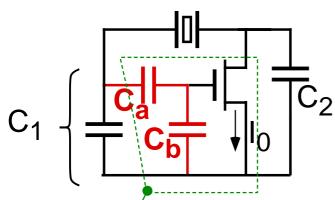
Yields bias current  $I_0$  as a function of amplitude  $V_1$ :



OSC-11b

#### LARGER AMPLITUDES

- Limited overdrive to avoid excessive distortion
- Use capacitive input attenuator C<sub>a</sub>-C<sub>b</sub>:

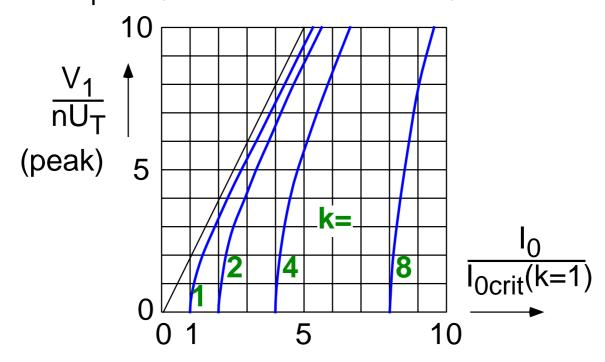


- Attenuation  $1/k = \frac{C_a}{C_b + C_a}$   $C_b$  includes  $C_G$  In weak inversion:

$$C_G = C_{ox}(1-1/n)$$

equivalent to transistor with  $U_T \Rightarrow kU_T$ 

Result for transistor in weak inversion:  $g_{\text{mequ}} = I_0/(knU_T)$ , thus  $V_1$  and  $I_0$  amplified by **k**.



- Alternative solution: **strong** inversion
  - might be necessary for f>10MHz (large W/L $\rightarrow$  large C<sub>1</sub> and C<sub>2</sub>)

E. Vittoz. 2001-

#### AMPL. LIM. BY i<sub>D</sub>(v<sub>G</sub>) IN STRONG INVERSION

Assumption: AC signal at gate sinusoidal:

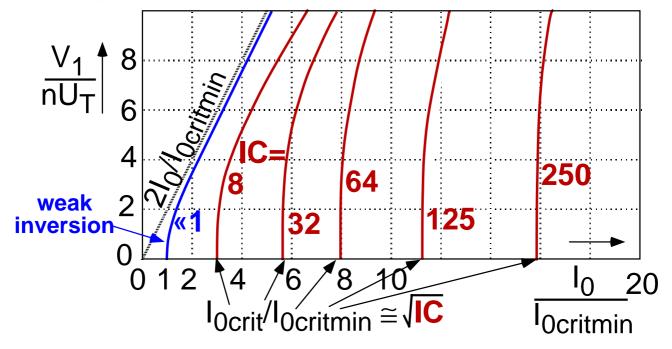
$$v_G = V_0 + V_1 \sin(\omega t)$$

results in:  $i_D = I_0 + I_1 \sin(\omega t) + \text{harmonics}$ 

•  $I_1/V_1 = g_{m1}(V_1) = g_{mcrit}$  can be calculated numerically by using a continuous model for saturated MOS transistor:

$$i_D = I_S \ln^2(1 + e^{V/2})$$

where  $v = (v_{GS}-V_T)/(nU_T)$  and  $I_S = 2n\beta U_T^2$  this yields [L.Astier, 1987]:



 $V_1$  = peak voltage amplitude at gate of transistor

 $I_0 = DC$  bias current of transistor

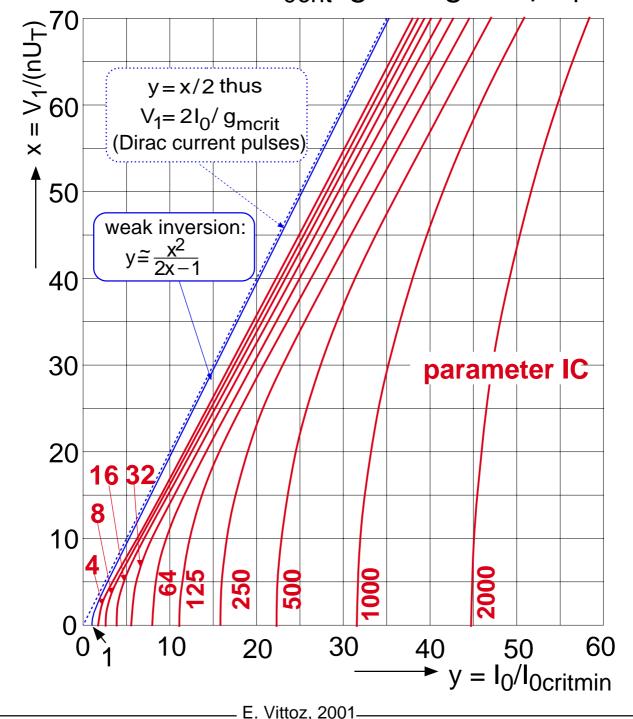
 $I_{Ocritmin} = nU_{T}g_{mcrit}$  (weak inversion)

 $IC = I_{Ocrit}/I_{S} = inversion coefficient at I_{Ocrit}$ 

#### CHART FOR LARGE AMPLITUDES

[L.Astier, 1987]

- Assumptions: gate voltage sinusoidal (peak V<sub>1</sub>)
  - transistor always saturated
  - constant mobility
  - constant Q, linear Z<sub>1</sub>,Z<sub>2</sub> and Z<sub>3</sub>
- Definitions:
   I<sub>0critmin</sub>=I<sub>0crit</sub> in weak inversion
  - IC =  $I_{0crit}/I_{S}$  with  $I_{S} = 2n\beta U_{T}^{2}$



#### **BASIC DESIGN PROCEDURE**

-	• • •	
MAIN	criteria	ref.OSC
1114111	CHUELIA	161727
HILL	Olitolia	101100

1. Select crystal resonator	frequency
·	temp. stability
	cost, size

2. Choose value of $C_1=C_2$ precision	12
power	8a

"circle" 8a

3. Calculate  $p_0$  and  $\omega_m = \omega_0 (1-p_0)$  8a

**4.** Calculate g<sub>mcrit</sub> 8a, 9

I<sub>Ocritmin</sub> 11c

**5.** Fix ampl. of oscill.  $V_1$  too small:

- phase noise 13b

- amplification 14a

- jitter of amplif.

too large:

power

- aging

6. Fix amount of overdrive too small: 11d

- large I<sub>0</sub>/V<sub>1</sub>

too large:

- poor stability 12

- risk of overtone 14

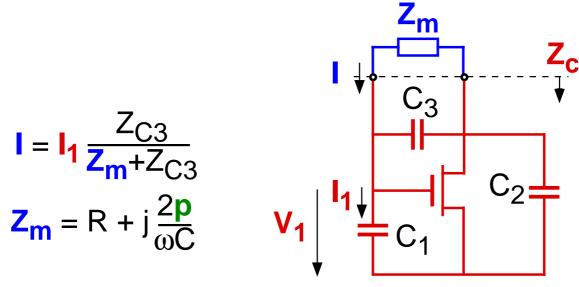
7. Select  $IC=I_{0crit}/I_{S}$  from 5. and 6. 11d

8. Calculate  $I_{0crit}$ ,  $I_0$ ,  $I_S=2n\beta U_T^2$ ,  $\beta$ , W/L 11d

9. Calculate energy E<sub>m</sub> and phase noise 13a,b

10. Return to 2, 5 or 6, or detailed design.

#### **ENERGY OF MECHANICAL OSCILLATION**



(I, I<sub>1</sub> and V<sub>1</sub> are complex RMS values)

Thus: 
$$I = I_1 \frac{-j/\omega C_3}{R + 2pj/\omega C - j/\omega C_3}$$

Then: 
$$I \cong I_1 \left(1 + \frac{C_3}{C_s}\right)$$
 where  $C_s = \frac{C_1 C_2}{C_1 + C_2}$ 

where 
$$C_s = \frac{C_1 C_2}{C_1 + C_2}$$

$$I \cong j\omega C_1 V_1 \left(1 + \frac{C_3}{C_s}\right)$$

 $I \cong j\omega C_1 V_1 \left(1 + \frac{C_3}{C_s}\right)$  current through motional impedance  $Z_m$ 

Mechanical energy: 
$$E_{m} = \frac{|\mathbf{I}|^2}{\omega^2 C} = \frac{C_1^2 |\mathbf{V_1}|^2}{C} \left(1 + \frac{C_3}{C_s}\right)^2$$

#### PHASE NOISE

- Simple model [Leeson, 1966](linear, time invariant)
- Equivalent circuit at stable oscillation

noise spectral density of

resonator circuit 4kTR  $4kT\gamma R$  stable oscillation  $R = |Z_{c(1)}| = -R$ 

Impedance loading the noise sources:

$$\mathbf{Z} = 2j\omega L \left(\frac{f - f_0}{f_0}\right) = 2jQR \left(\frac{f - f_0}{f_0}\right)$$
 for  $|f - f_0| \ll f_0$ 

where f<sub>0</sub> is the frequency of oscillation

Noise current I<sub>N</sub> circulating in the loop:

$$\frac{dI_N^2}{df} = \frac{4kT(1+\gamma)R}{|\mathbf{Z}|^2} = \frac{(1+\gamma)kT}{Q^2R} \left(\frac{f_0}{f-f_0}\right)^2$$

Phase noise spectral density:

$$\frac{d\phi_N^2}{df} = \frac{1}{2} \frac{dI_N^2/df}{I^2}$$
 (half phase noise, half amplitude noise)

$$\frac{d\phi_N^2}{df} = \frac{(1+\gamma)kT}{2Q^2P_m} \left(\frac{f_0}{f-f_0}\right)^2 = \frac{(1+\gamma)kT}{2\omega QE_m} \left(\frac{f_0}{f-f_0}\right)^2$$

 Nonlinear, time-variant: noise may added, including 1/f [Hajimiri-Lee,1999]

#### FREQUENCY INSTABILITY

#### **Cause**

#### **Remedy**

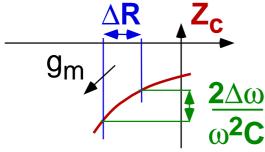
- a. Crystal resonator
- Aging
- Temperature

- Pre-aging.
- Better cut
- analog or digital compensation.
- b. Nonlinear effects in circuit (variations with V<sub>B</sub>, V<sub>T</sub>, T)
- Nonlinear Z<sub>1</sub>, Z<sub>2</sub> or Z<sub>3</sub>
- Nonlinear I<sub>D</sub>(V<sub>G</sub>)

- Keep trans.in saturation
- avoid C(V) effects.
- Reduce overdrive
- stabilize amplitude
- increase |Z<sub>3</sub>|.

#### c. Variation of linear effects

Variation of R~1/Q

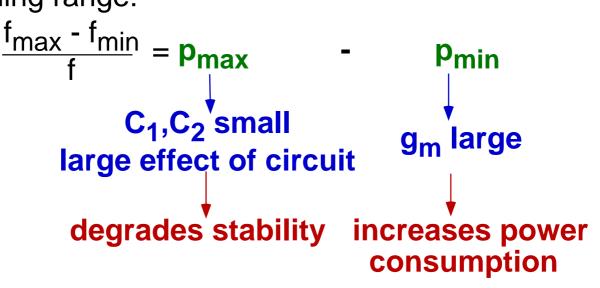


- Variation of losses
- Variation of C<sub>1</sub>, C<sub>2</sub>, C<sub>3</sub>

- Increase Q
- reduce losses in circuit.
- increase  $\frac{C_1C_2}{C_3(C_1+C_2)}$
- Reduce losses
- Decrease pulling p
- avoid C(V) effects
- stabilize V<sub>B</sub>.

#### FREQUENCY TUNING

- On the resonator:
   precision limited to a few 10<sup>-5</sup>.
- By C<sub>1</sub> and/or C<sub>2</sub> in the circuit: tuning range:



- Digital tuning:
  - adjust the ratio of subsequent counters
  - inhibit an adequate percentage of pulses requires a few bits of memory:

pad bondings RAM

E<sup>2</sup>PROM.

#### ELIMINATION OF UNWANTED MODES

- A resonator has always several mech. modes (parallel series resonator in model).
- One mode is wanted (WM)
- All other modes are unwanted (UM).

$$g_{mcrit} = \sim \frac{\omega}{QC} (C_1 + 2C_3)^2 \text{ (for } C_2 = C_1)$$

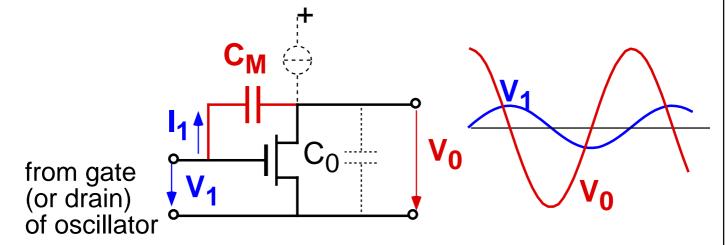
$$= \omega^2 R \text{ same for all modes}$$

#### activity different for each mode

- a. Non-distorting amplitude limitation
  - No interaction between modes; g<sub>m</sub> decreases until the most active reaches critical amplitude.
  - WM ensured if  $\omega^2 R|_{WM} < \omega^2 R|_{UM}$
- b. Distorting amplitude limitation
  - Possible interaction between modes (very complicated).
  - Safe solution:  $g_{mcrit}|_{WM} < g_{m} < g_{mcrit}|_{UM}$  requires  $\omega^{2}R|_{WM} \ll \omega^{2}R|_{UM}$
- c. Selection of WM of lesser activity
  - frequency selective  $Z_c \rightarrow$  degrades stability.
    - low- or high-pass for large difference in  $\omega_{\text{m}}$
    - LC bandpass to select a particular overtone

#### LOADING BY OUTPUT AMPLIFIER

Elementary voltage amplifier, gain A = |V<sub>0</sub>|/|V<sub>1</sub>|



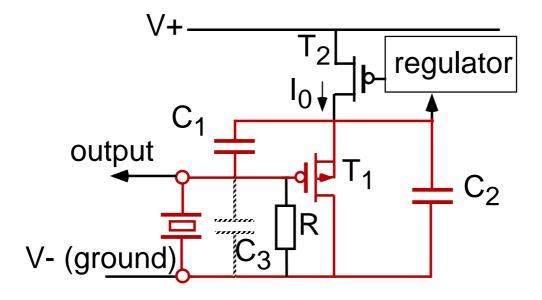
- Capacitive load: V<sub>0</sub> = j AV<sub>1</sub> (complex gain)
- Miller capacitance C<sub>M</sub>, thus, for A»1
   I<sub>1</sub>=-jωC<sub>M</sub>V<sub>0</sub> = ωAC<sub>M</sub>V<sub>1</sub>, in phase with V<sub>1</sub>
- Input conductance  $G_1 = I_1/V_1 = \omega C_M A$  may be large if  $C_M$  and A large.

significant loss in oscillator

 Increasing V<sub>1</sub> requires more current in lossless oscillator, but reduces loss due to G<sub>1</sub>: trade-off.

#### GROUNDED-DRAIN OSCILLATOR

[Luescher, 1968, Santos-Meyer, 1984]

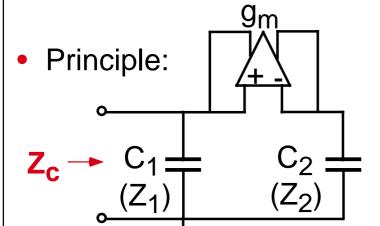


 $T_1$  active, biased by R and current source  $T_2$ .

- + One single pin for resonator ("1-pin oscillator").
- + Doubled output amplitude.
- Increased C<sub>3</sub>: decreases stability and/or increases power.
- T<sub>1</sub> must be put in a separate well connected to its source; otherwise an additional conductance g<sub>m</sub>(n-1) is added to G<sub>2</sub> (large increase of losses).

#### ONE-PIN OSCILLATOR WITH GROUNDED C's

[van den Homberg, 1998/99]



$$\mathbf{Z_c} = \frac{Z_1 + g_m Z_1 Z_2}{1 + g_m (Z_1 - Z_2)}$$

bilinear function of g<sub>m</sub>

• For 
$$Z_i = \frac{1}{j\omega C_i}$$
:

Z-plane

Necessary condition for oscill.:

$$R < \frac{C_1/C_2}{\omega(C_1-C_2)} \rightarrow Q > \frac{C_1-C_2}{C.C_1/C_2}$$

If realized with large margin:

$$\mathbf{p_0} = \frac{\mathbf{C}}{2\mathbf{C_1}}$$

$$g_{\text{mcrit}} = \frac{\omega}{QC} C_1 C_2 = \frac{\omega C}{4Qp_0^2} \frac{C_2}{C_1}$$

 $g_m$  $\mathbf{Z_c}(\mathbf{g_m})$  $g_{\text{mcrit}} = \frac{\omega}{QC} C_1 C_2 = \frac{\omega C}{4Qp_0^2} \frac{C_2}{C_1} - \frac{1}{\omega(C_1 - C_2)}$ 

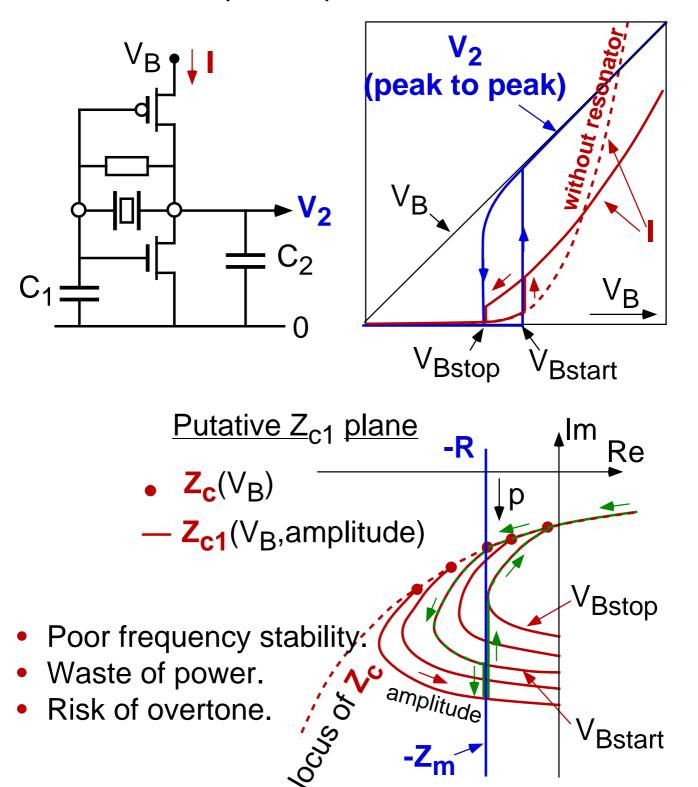
Condition for stability: (pole of Zc with negative real part)

$$C_1 > C_2$$

radius of circle reduced for increased margin

#### **CMOS-INVERTER OSCILLATOR**

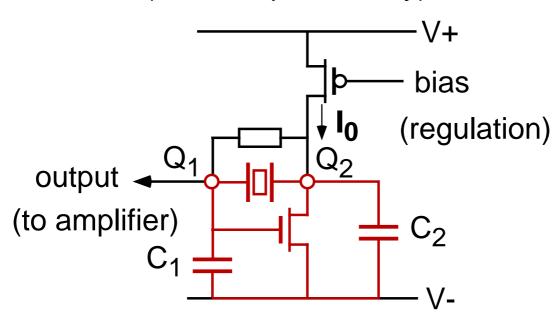
- a simple but poor solution -



Possible improvement by resistors in the drains.

#### GROUNDED-SOURCE OSCILLATOR

(non-complementary)



For fixed bias current I<sub>0</sub>:

Margin needed for variations of Q and process

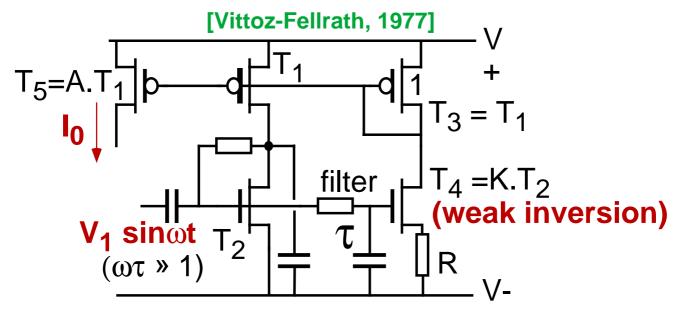
possible overdrive

waste of power limitation by distortion

#### Best:

Low-level amplitude regulation+ output amplifier

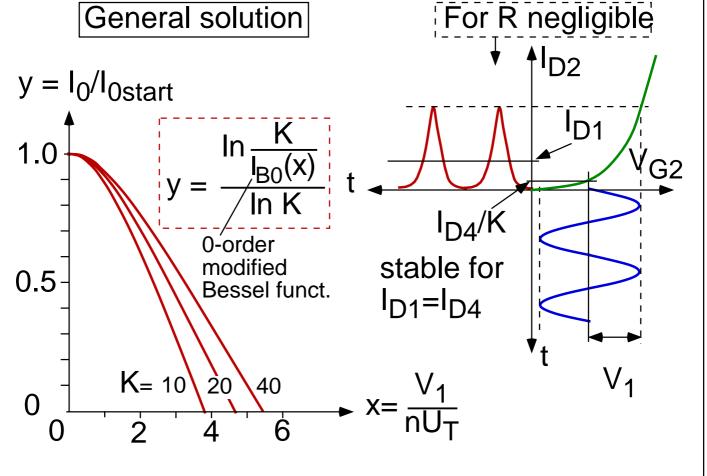
#### AMPLITUDE REGULATOR



No AC input voltage (V<sub>1</sub>=0):

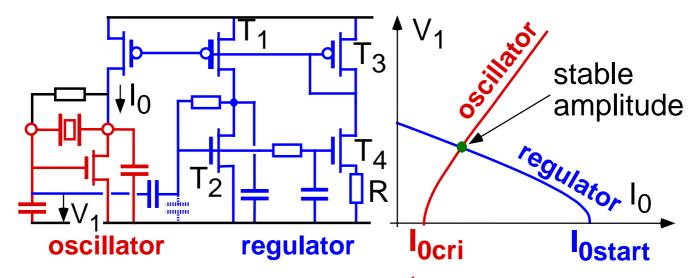
$$I_0 = I_{0start} = \frac{AU_T}{R}$$
 InK (start-up current)

• For V<sub>1</sub>>0:

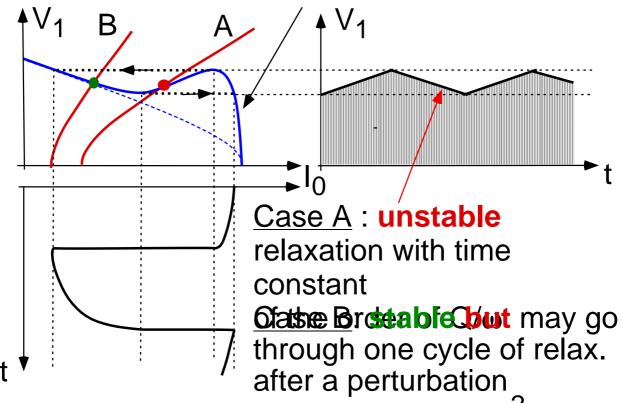


E. Vittoz, 2001-

#### AMPLITUDE REGULATING LOOP



 Effect of T<sub>2</sub>-T<sub>4</sub> entering strong inversion: distortion of the regulator's characteristics

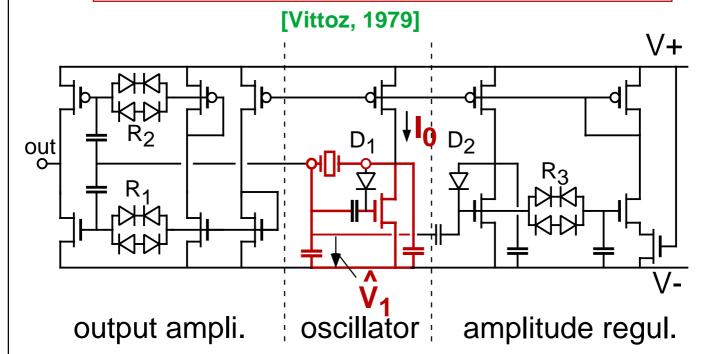


• Design criterion:  $i_{D2max} < I_{S2} = 2n\beta_2 U_T^2$  (too strict)

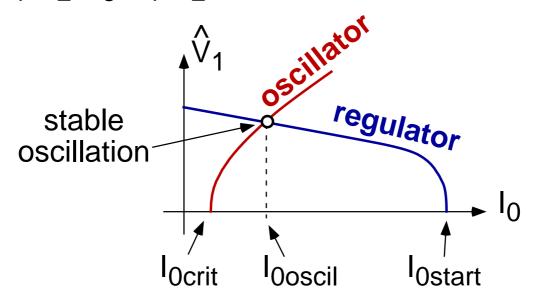
semi-empirical:

$$R > \frac{2\beta_1/\beta_3}{\beta_2 n U_T}$$

#### MICROPOWER CRYSTAL OSCILLATOR



 $R_1, R_2, R_3, D_1, D_2$ : lateral diodes in poly layer



Example: f=32KHz

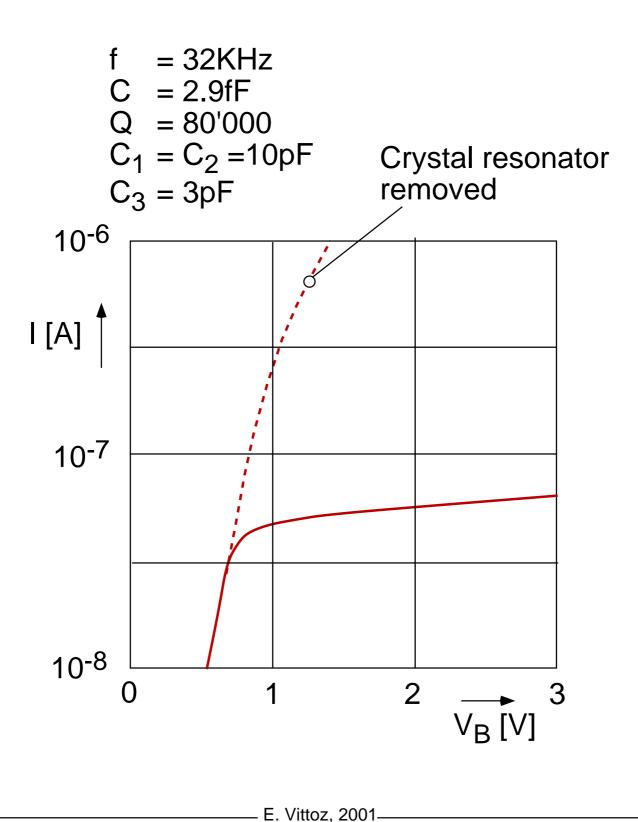
 $V_B=1$  to 3 V

 $I_{tot}$ = 20 to 100nA (depends on  $C_1, C_2, Q$ )

no external component except crystal.

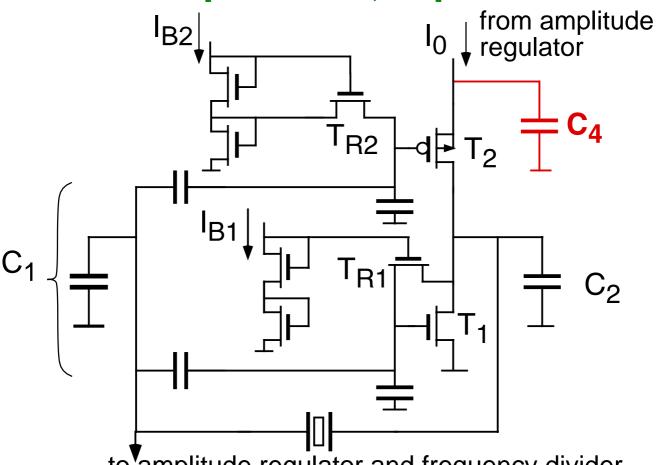
#### **CURRENT DRAIN**

#### of micropower crystal oscillator



## VERY LOW-POWER 2MHZ OSCILLATOR

#### [Aebischer et al, 1997]

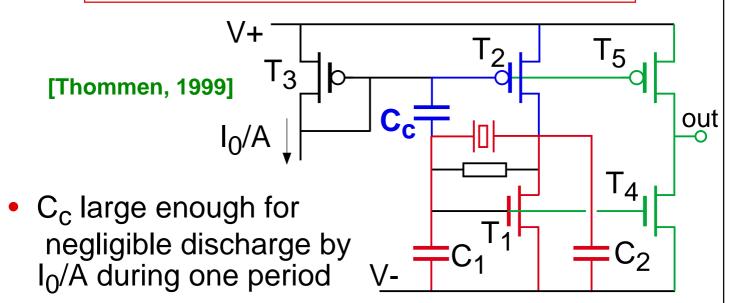


to amplitude regulator and frequency divider

- Currrent controlled CMOS inverter T<sub>1</sub>-T<sub>2</sub>
  - gates separately biased by T<sub>R1</sub>-T<sub>R2</sub>
    - controlled by bias I<sub>B1</sub>-I<sub>B2</sub>
  - source of T<sub>2</sub> AC grounded by C<sub>4</sub>, with  $\omega C_4 \gg g_{ms2}$
- 2.1 MHz ZT cut quartz, C=0.5fF, Q=300-900K  $C_1 = C_2 = 2.5 pF, C_3 = 0.7 pF, C_4 = 10 pF$

I = 60-180nA (core oscillator only) (oscill.+freq. divider+ dig. tuning)

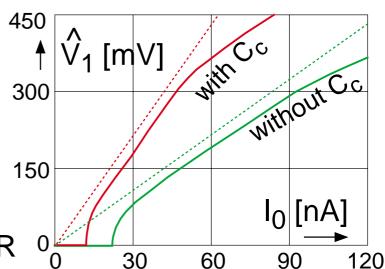
#### COMPACT PUSH-PULL OSCILLATOR



- Average current I<sub>0</sub> through T<sub>1</sub> and T<sub>3</sub>:
  - imposed by T<sub>3</sub>
  - from amplitude regulator
- Instantaneous current in T<sub>3</sub>
  - proportional to that in T<sub>2</sub>
  - creates a loss conductance, thus:
  - effect. trans. of T<sub>2</sub> for fundamental: g<sub>m2(1)</sub>(1-1/A)
- Output amplifier T<sub>4</sub>-T<sub>5</sub> directly coupled to T<sub>1</sub>-T<sub>2</sub>

Experimental results:

$$\begin{array}{ll} f & = 32 \text{ kHz} \\ R & = 35 \text{ k}\Omega \\ A & = 16 \\ C_1 & = 12.3 \text{ pF} \\ C_2 & = 24.6 \text{ pF} \\ C_3 & = 1 \text{pF} \\ V_{Bmin} & = 0.7 V \end{array}$$



Drawback:poor PSRR

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